

LL103ATHUR LL103C

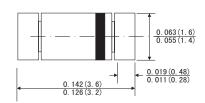
SMALL SIGNAL SCHOTTKY DIODES

FEATURES

- · For general purpose applications
- The LL103 series is a Metal-on-silicon junction Schottky barrier device which
 is protected by a PN junction guard ring. The low forward voltage drop and fast
 switching make it ideal for protection of MOS devices, steering, biasing, and coupling
 diodes for fast switching and low logic level applications. Other applications are click
 suppressions, efficient full wave bridges in telephone subsets, and blocking diodes in
 rechargeable low voltage battery systems.
- These diodes are also available in the DO-35 case with the type designation SD103A to SD103C.
- · High temperature soldering guaranteed:260°C/10 seconds at terminals
- · Component in accordance to RoHS 2011/65/EU

MiniMELF





Dimensions in inches and (millimeters)

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MECHANICAL DATA

- · Case: MiniMELF glass case(SOD-80)
- · Polarity: Color band denotes cathode end
- · Weight: Approx. 0.05 gram

ABSOLUTE RATINGS(LIMITING VALUES)

		Symbols	Value	Units			
Peak Reverse Voltage	LL 103A LL 103B LL 103C	Vrrm Vrrm Vrrm	40 30 20	V V			
Power Dissipation (infinite Heat Sink)		Ptot	400 1)	mW			
Maximum Single cycle surge 60Hz sine wave		IFSM	15	Α			
Junction temperature		TJ	125	°C			
Storage Temperature Range		Тѕтс	-55 to+150	°C			
1) Valid provided that electrodes are kept at ambient temperature							

ELECTRICAL CHARACTERISTICS

(Ratings at 25°C ambient temperature unless otherwise specified)

	Symbols	Min.	Тур.	Max.	Unis
Leakage current at VR=30V	lr lr lr			5 5 5	μΑ μΑ μΑ
Forward voltage drop at Ir=20mA Ir=200mA	VF VF			0.37 0.6	V V
Junction Capacitance at V _R =0V ,f=1MHz	Cı		50		pF
Reverse Recovery time at IF=IR=50mA,recover to 200mA recover to 0.1 IR	trr		10		ns

RATINGS AND CHARACTERISTIC CURVES LL103A THRU LL103C

Figure 1. Typical variation of forward current vs. Forward. Voltage for primary conduction through the schottky barrier

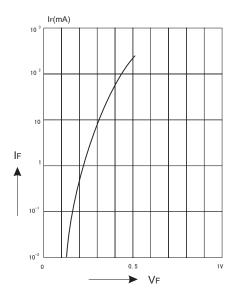
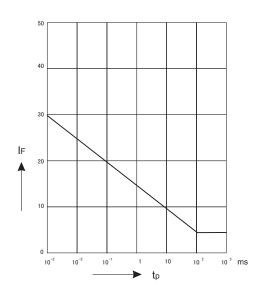


Figure 3. Typical non repetitive forward surge current versus pulse width



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Figure 2. Typical high current forward conduction curve tp=300ms,duty cycle=2%

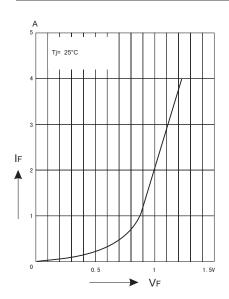
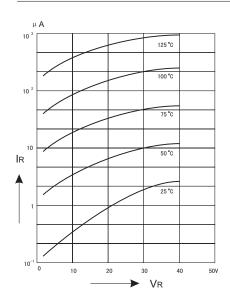


Figure 4. Typical variation of reverse current at various temperatures



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Figure 5. Blocking deration versus temperature at various average forward currents

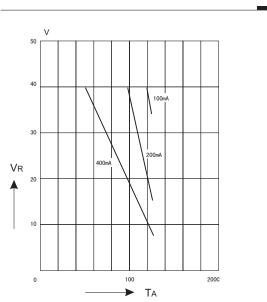


Figure 6. Typical capacitance versus reverse voltage

